

Appl. No. 10/092,465  
Amdt. Dated January 20, 2004  
Reply to Office action of October 17, 2003

**Listing of Claims:**

1. (Canceled)
2. (Canceled)
3. (Canceled)
4. (Canceled)
5. (Canceled)
6. (Canceled)
7. (Canceled)
8. (Canceled)
9. (Currently amended) A platinum sputtering target material, wherein said target material ~~containing~~ contains columnar crystals grown in a direction normal to a sputtering surface, and a ratio of an integral intensity of a (200) face to that of another arbitrary crystal face as determined by X-ray diffractometry is greater than the corresponding ratio as measured for a powder platinum sample.
10. (Currently amended) A ruthenium sputtering target material, wherein said target material ~~containing~~ contains columnar crystals grown in a direction normal to a sputtering surface, and a ratio of an integral intensity of a (112) face to that of another arbitrary crystal face as determined

by X-ray diffractometry is greater than the corresponding ratio as measured for a powder ruthenium sample.

11. (Currently amended) A ruthenium sputtering target material, wherein said target material ~~containing~~ contains columnar crystals grown in a direction normal to a sputtering surface, and a ratio of an integral intensity of a (002) face to that of another arbitrary crystal face as determined by X-ray diffractometry is greater than the corresponding ratio as measured for a powder ruthenium sample.

12. (Currently amended) A ruthenium sputtering target material, wherein said target material ~~containing~~ contains columnar crystals grown in a direction normal to a sputtering surface, and a ratio of an integral intensity of a (004) face to that of another arbitrary crystal face as determined by X-ray diffractometry is greater than the corresponding ratio as measured for a powder ruthenium sample.

13. (Currently amended) An iridium sputtering target material, wherein said target material ~~containing~~ contains columnar crystals grown in a direction normal to a sputtering surface, and a ratio of an integral intensity of a (220) face to that of another arbitrary crystal face as determined by X-ray diffractometry is greater than the corresponding ratio as measured for a powder iridium sample.

14. (Previously presented) A sputtering target material according to claim 9, wherein a crystallographic microstructure containing the columnar crystals is electrodeposited from a solution containing a precious metal salt.

15. (Previously presented) A sputtering target material according to claim 10, wherein a crystallographic microstructure containing the columnar crystals is electrodeposited from a solution containing a precious metal salt.

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16. (Previously presented) A sputtering target material according to claim 11, wherein a crystallographic microstructure containing the columnar crystals is electrodeposited from a solution containing a precious metal salt.

17. (Previously presented) A sputtering target material according to claim 12, wherein a crystallographic microstructure containing the columnar crystals is electrodeposited from a solution containing a precious metal salt.

18. (Previously presented) A sputtering target material according to claim 13, wherein a crystallographic microstructure containing the columnar crystals is electrodeposited from a solution containing a precious metal salt.

19. (Canceled)

20. (Canceled)

21. (Canceled)

22. (Canceled)

23. (Canceled)